



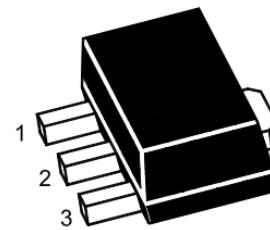
**迈拓电子**  
MAITUO ELECTRONIC

## 2SC3357

### NPN Transistors

#### ■ Features

- Low noise and high gain
- High power gain
- Large  $P_{tot}$



1.Base 2.Collector 3.Emitter

**SOT-89-3L**

#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	20	V
Collector - Emitter Voltage	$V_{CEO}$	12	
Emitter - Base Voltage	$V_{EBO}$	3	
Collector Current - Continuous	$I_C$	100	mA
Collector Power Dissipation	$P_C$	1.2	W
Junction to Ambient Resistance	$R_{th(j-a)}$	62.5	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	20			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	12			
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	3			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 20\text{V}, I_E = 0$			1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 3\text{V}, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5\text{mA}$			0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5\text{mA}$			1.2	
DC current gain (Note.1)	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$	50		250	
Insertion Power Gain	$ S_{21e} ^2$	$V_{CE} = 10\text{V}, I_C = 20\text{mA}, f = 1\text{GHz}$		9		dB
Noise Figure	NF	$V_{CE} = 10\text{V}, I_C = 7\text{mA}, f = 1\text{GHz}$		1.1		
		$V_{CE} = 10\text{V}, I_C = 40\text{mA}, f = 1\text{GHz}$		1.8	3	
Reverse Transfer Capacitance	$C_{re}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$			1	pF
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$		6.5		GHz

Note.1: Pulse measurement:  $PW \leq 350 \text{ us}$ , Duty Cycle  $\leq 2\%$

#### ■ Classification of $h_{FE}$

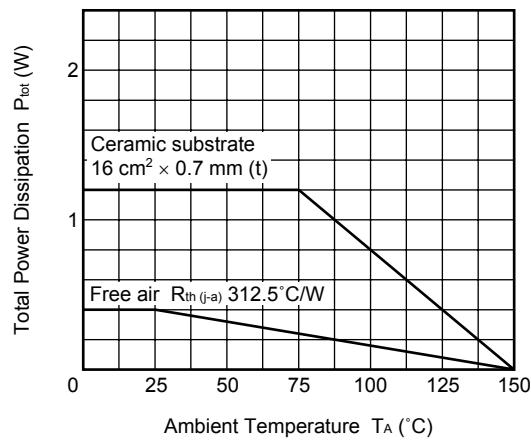
Type	2SC3357-F	2SC3357-E
Range	80-160	125-250
Marking	RF	RE



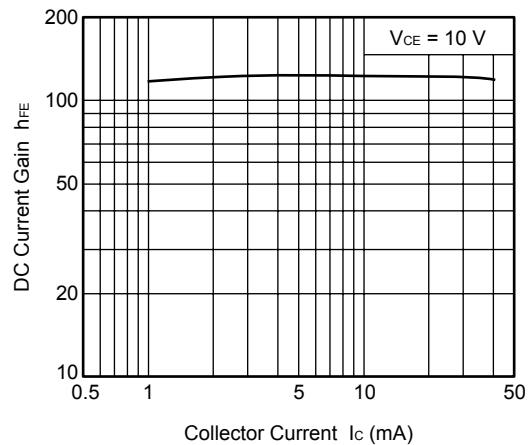
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## ■ Typical Characteristics

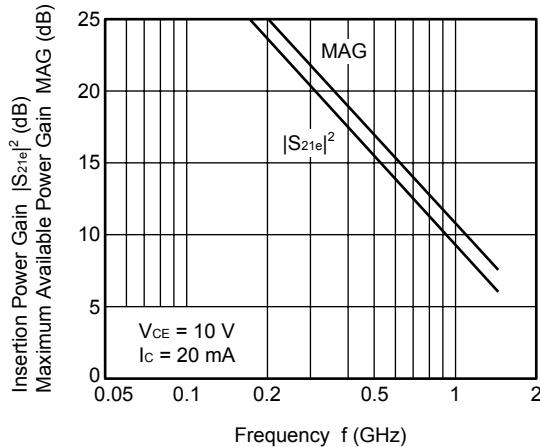
TOTAL POWER DISSIPATION  
vs. AMBIENT TEMPERATURE



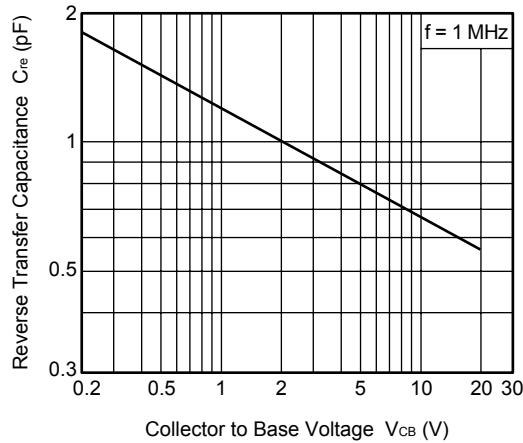
DC CURRENT GAIN vs.  
COLLECTOR CURRENT



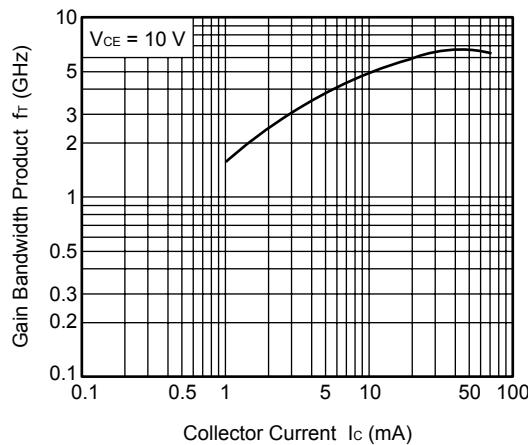
INSERTION POWER GAIN, MAG  
vs. FREQUENCY



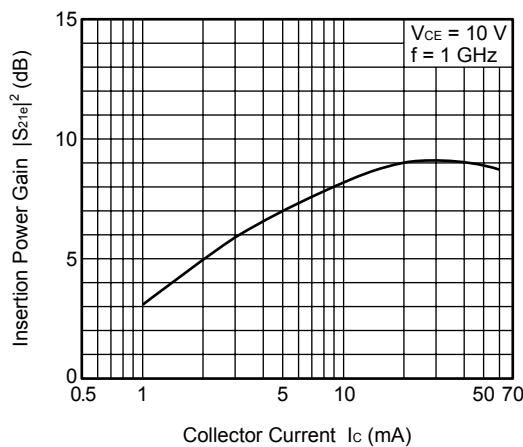
REVERSE TRANSFER CAPACITANCE  
vs. COLLECTOR TO BASE VOLTAGE



GAIN BANDWIDTH PRODUCT  
vs. COLLECTOR CURRENT



INSERTION POWER GAIN  
vs. COLLECTOR CURRENT

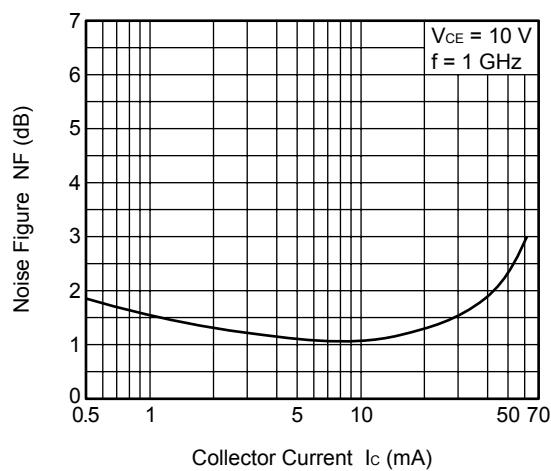




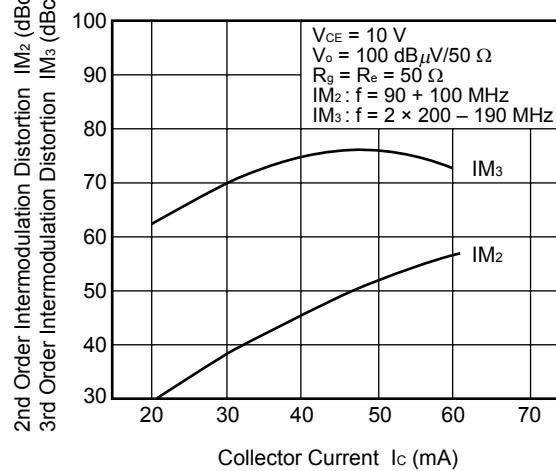
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### ■ Typical Characteristics

NOISE FIGURE vs.  
COLLECTOR CURRENT



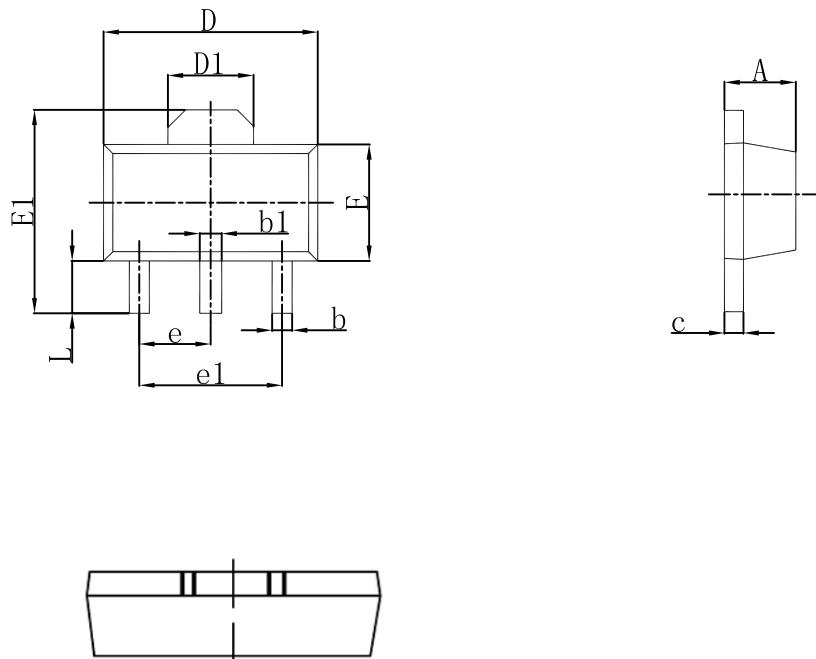
IM<sub>2</sub>, IM<sub>3</sub> vs. COLLECTOR CURRENT





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SOT-89-3L Outlines Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047